

## PolarP™ Power MOSFET

## IXTH90P10P IXTT90P10P

$$V_{DSS} = -100V$$

$$I_{D25} = -90A$$

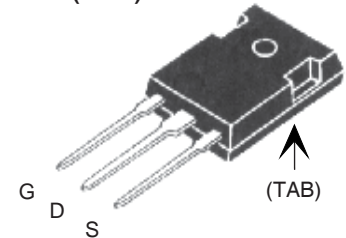
$$R_{DS(on)} \leq 25m\Omega$$

P-Channel Enhancement Mode  
Avalanche Rated

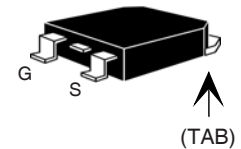


Symbol	Test Conditions	Maximum Ratings	
		Value	Unit
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	-100	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	-100	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$	- 90	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	- 225	A
$I_A$	$T_C = 25^\circ C$	- 90	A
$E_{AS}$	$T_C = 25^\circ C$	2.5	J
$dV/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	10	V/ns
$P_D$	$T_C = 25^\circ C$	462	W
$T_J$		- 55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		- 55 ... +150	$^\circ C$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$M_d$	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	5	g

TO-247 (IXTH)



TO-268 (IXTT)



G = Gate      D = Drain  
S = Source      TAB = Drain

### Features:

- International Standard Packages
- Avalanche Rated
- Fast Intrinsic Diode
- Rugged PolarP™ Process
- Low Package Inductance

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

### Applications

- High-Side Switches
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = -250\mu A$	-100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	- 2.0		- 4.0 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			- 25 $\mu A$ - 200 $\mu A$
$R_{DS(on)}$	$V_{GS} = -10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			25 m $\Omega$

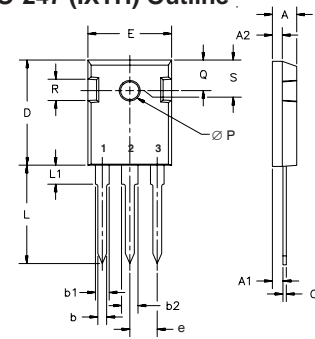
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = -10\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1	22	37	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = -25\text{V}$ , $f = 1\text{MHz}$		5800	pF
$C_{oss}$			1990	pF
$C_{rss}$			510	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = -10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 3\Omega$ (External)		25	ns
$t_r$			77	ns
$t_{d(off)}$			54	ns
$t_f$			32	ns
$Q_{g(on)}$	$V_{GS} = -10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		120	nC
$Q_{gs}$			23	nC
$Q_{gd}$			60	nC
$R_{thJC}$				$0.27^\circ\text{C/W}$
$R_{thCS}$	(TO-247)	0.21		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_s$	$V_{GS} = 0\text{V}$			- 90 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			- 360 A
$V_{SD}$	$I_F = -45\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1			- 3.3 V
$t_{rr}$	$I_F = -45\text{A}$ , $-di/dt = -100\text{A}/\mu\text{s}$ $V_R = -50\text{V}$ , $V_{GS} = 0\text{V}$		144	ns
$Q_{RM}$			0.92	$\mu\text{C}$
$I_{RM}$			-12.8	A

Note 1: Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

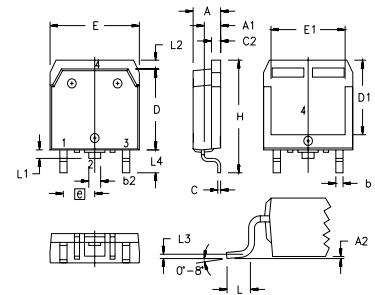
### TO-247 (IXTH) Outline



Terminals: 1 - Gate 2 - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L <sub>1</sub>		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216

### TO-268 (IXTT) Outline

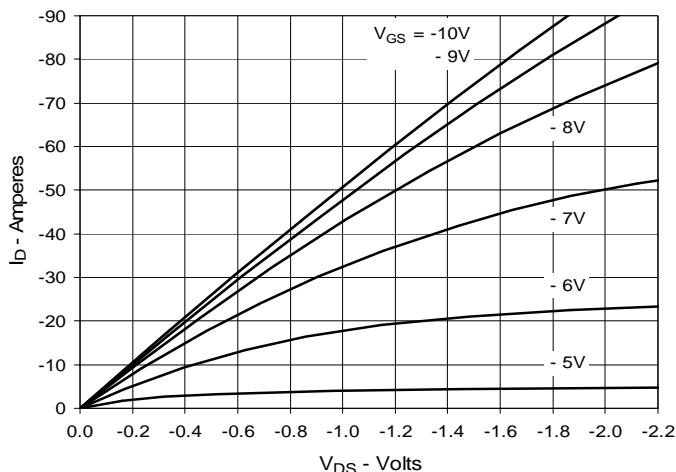


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

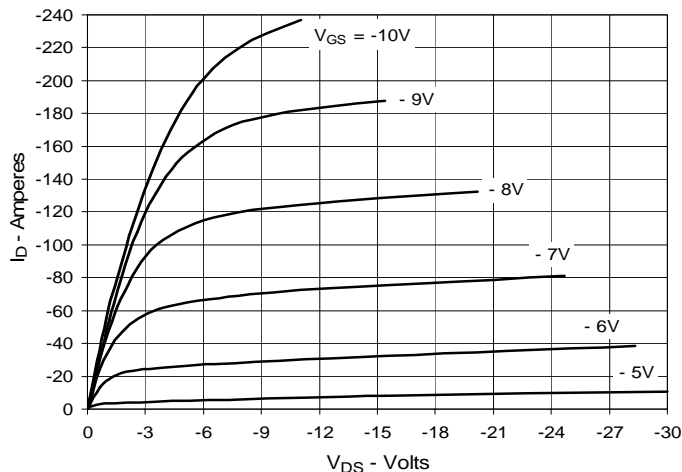
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2  
by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

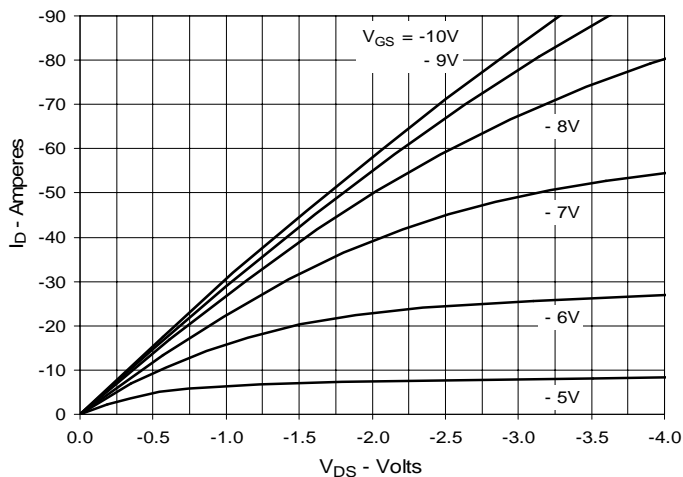
**Fig. 1. Output Characteristics @ 25°C**



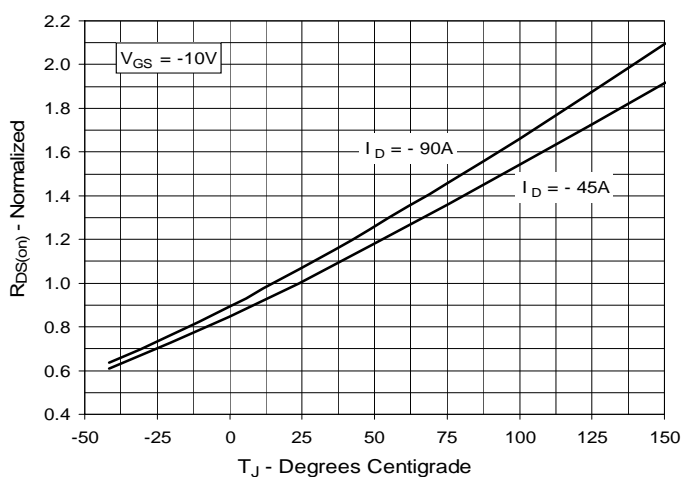
**Fig. 2. Extended Output Characteristics @ 25°C**



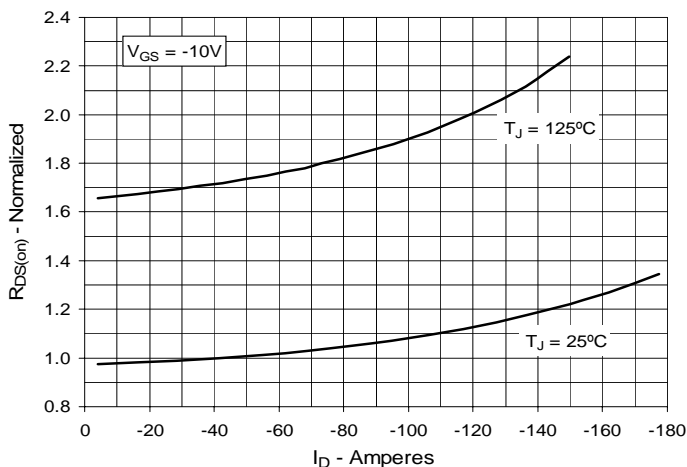
**Fig. 3. Output Characteristics @ 125°C**



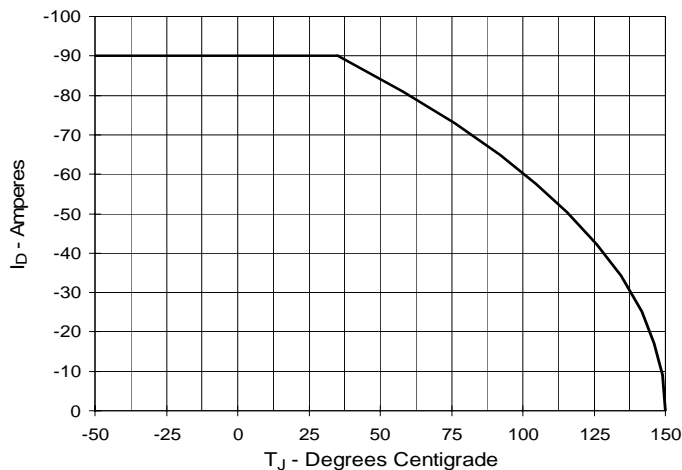
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = -45A$  vs. Junction Temperature**



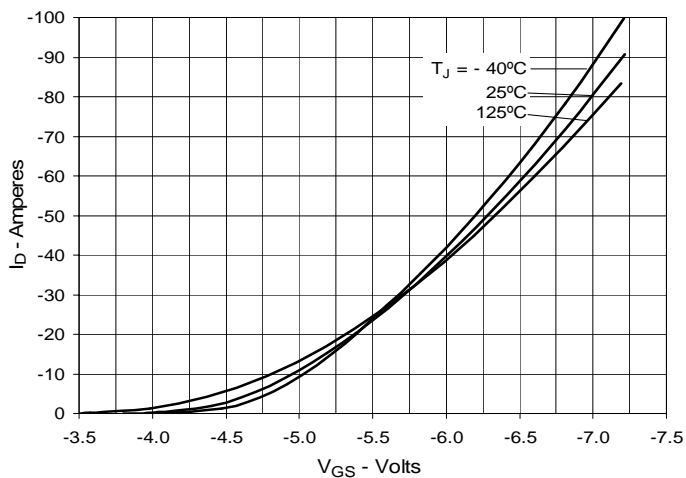
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = -45A$  vs. Drain Current**



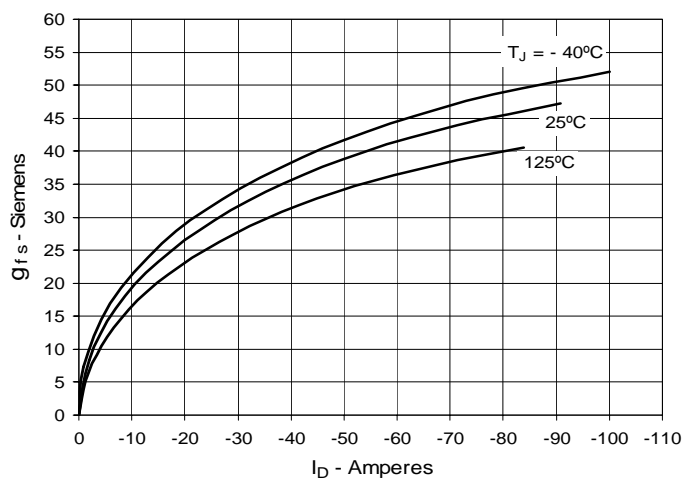
**Fig. 6. Maximum Drain Current vs. Case Temperature**



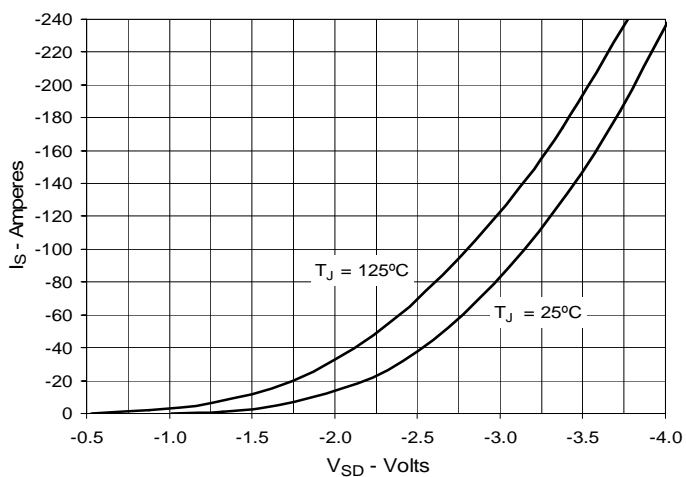
**Fig. 7. Input Admittance**



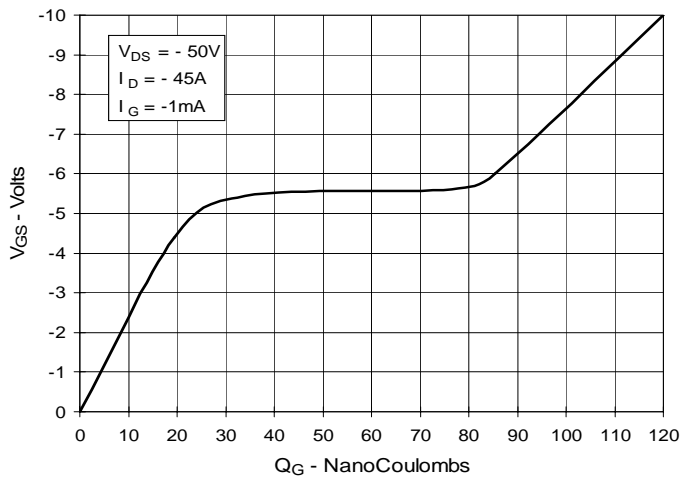
**Fig. 8. Transconductance**



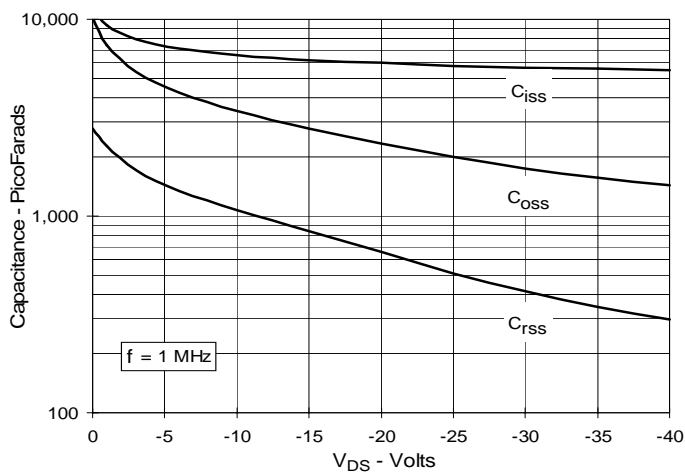
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



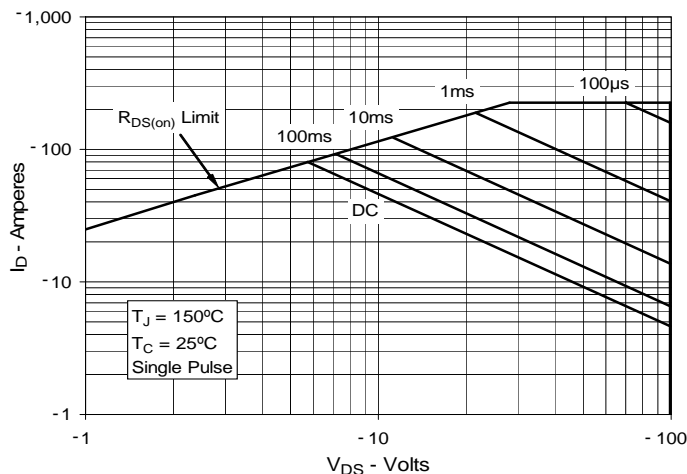
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

Fig. 13. Maximum Transient Thermal Impedance

